

TO-126 Plastic-Encapsulate Transistors

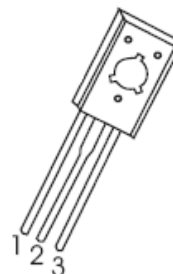
TRANSISTOR (NPN)

TO-126

Features:

- Power Dissipation

1. EMITTER
2. COLLECTOR
3. BASE



MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	60	V
V _{CE0}	Collector-Emitter Voltage	50	V
V _{EBO}	Emitter-Base Voltage	5	V
I _c	Collector Current -Continuous	3	A
P _c	Collector Power Dissipation	1.25	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C

ELECTRICAL CHARACTERISTICS (T_a=25 °C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR) _{CBO}	I _c = 100μA, I _E =0	60			V
Collector-emitter breakdown voltage	V(BR) _{CEO}	I _c = 10mA, I _B =0	50			V
Emitter-base breakdown voltage	V(BR) _{EBO}	I _E = 100μA, I _c =0	5			V
Collector cut-off current	I _{CBO}	V _{CB} = 40 V, I _E =0			1	μA
Collector cut-off current	I _{CEO}	V _{CE} = 30 V, I _B =0			10	μA
Emitter cut-off current	I _{EBO}	V _{EB} = 6 V, I _c =0			1	μA
DC current gain	h _{FE}	V _{CE} = 2 V, I _c = 1A	100		400	
Collector-emitter saturation voltage	V _{CE (sat)}	I _c = 2A, I _B = 0.2 A			0.5	V
Base-emitter saturation voltage	V _{BE (sat)}	I _c = 2A, I _B = 0.2 A			1.5	V
Transition frequency	f _T	V _{CE} = 5V, I _c =0.1A f =10MHz		90		MHz

CLASSIFICATION OF h_{FE}

Rank	O	Y	GR
Range	100-200	200-300	300-400

Typical Characteristics

